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TO-220 .> / / x N ?ú 3 « | • ’ož

N-CHANNEL MOSFET in a TO-220 Plastic Package.

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V_{DS} (V) = 100V I_D =130A (V_{GS} = f 20V)

8*9 54& < ‡ S S : _ V S S

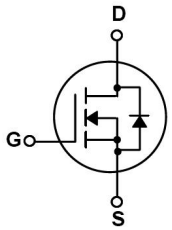
—)í D }ož HF Product.

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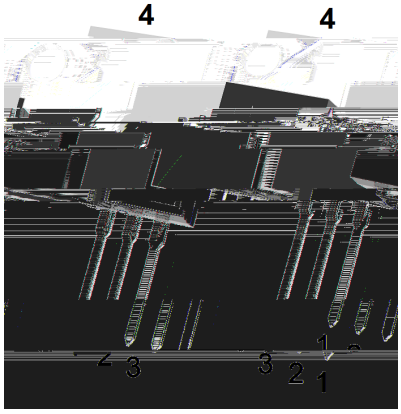
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Motor drivers, DC - DC Converter.

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PIN1 y G PIN 2o•4 y D PIN 3 y S

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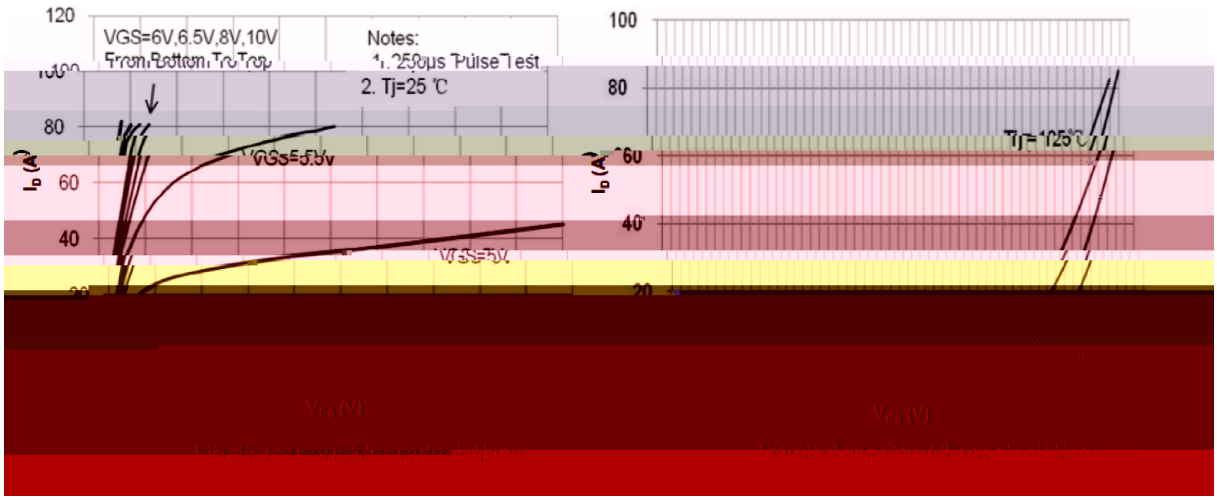
See Marking Instructions.

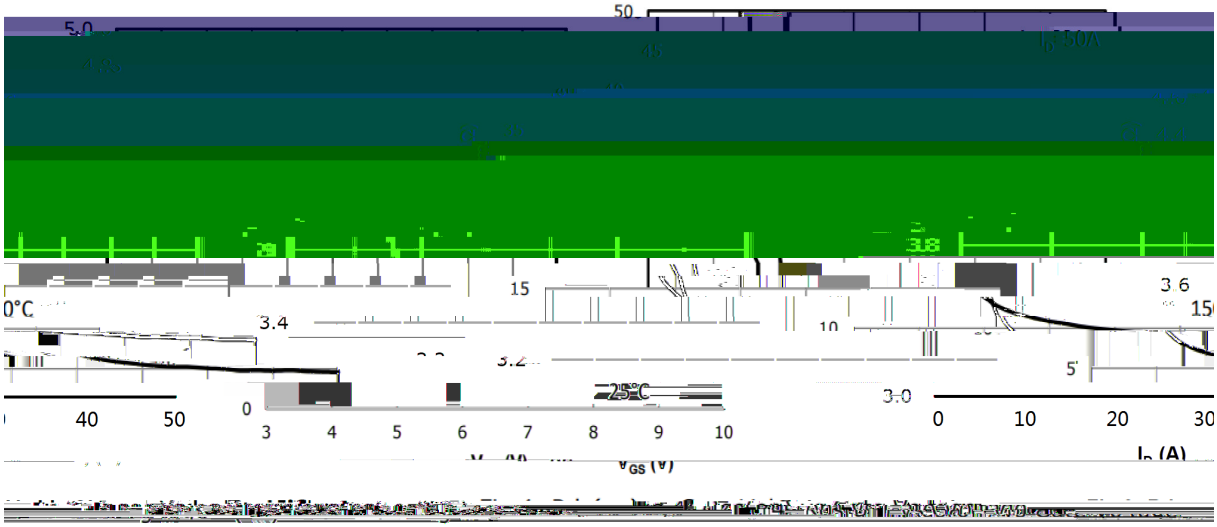
@ ƒ Parameter	… Z Symbol	ƒ › Rating	% y Unit
Drain-Source Voltage	V_{DSS}	100	V
Drain Current	I_D(Tc=25)	130	A
	I_D(Tc=100)	85	A
Pulsed Drain Current	I_{DM}	480	A
Gate-Source Voltage	V_{GS}	f 20	V
Single Pulsed Avalanche Energy(L=0.3mH)	E_{AS}	430	mJ
Total Power Dissipation	P_D(Tc=25)	178	W
Junction and Storage Temperature Range	T_J,T_{STG}	-55 to 150	-
Thermal Resistance-Junction to Ambient**	R $_{JA}$	64	- /W
Thermal Resistance-Junction to Case	R $_{JC}$	0.7	

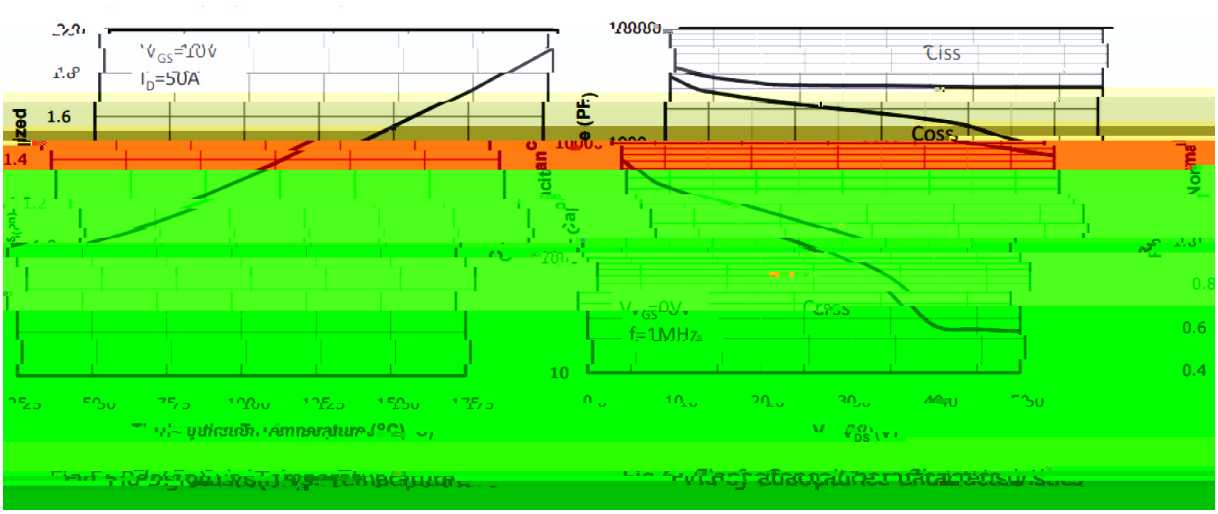
@ ƒ Parameter	… Z Symbol	y ¡ Ú ^ Test Conditions	Â 4 › Min	Á º › Typ	Â Ý › Max	% y Unit
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V I_D=250 A	100			V
Drain Leakage Current	I_{DSS}	V_{DS}=100V V_{GS}=0V			1	A
Gate Leakage Current	I_{GSS}	V_{GS}=±20V V_{DS}=0V				

@ ƒ Parameter	… Z Symbol	y ¡ Ú ^ Test Conditions	Â 4 › Min	Á º › Typ	Â Ý › Max	% y Unit
Turn-On Delay Time	t					

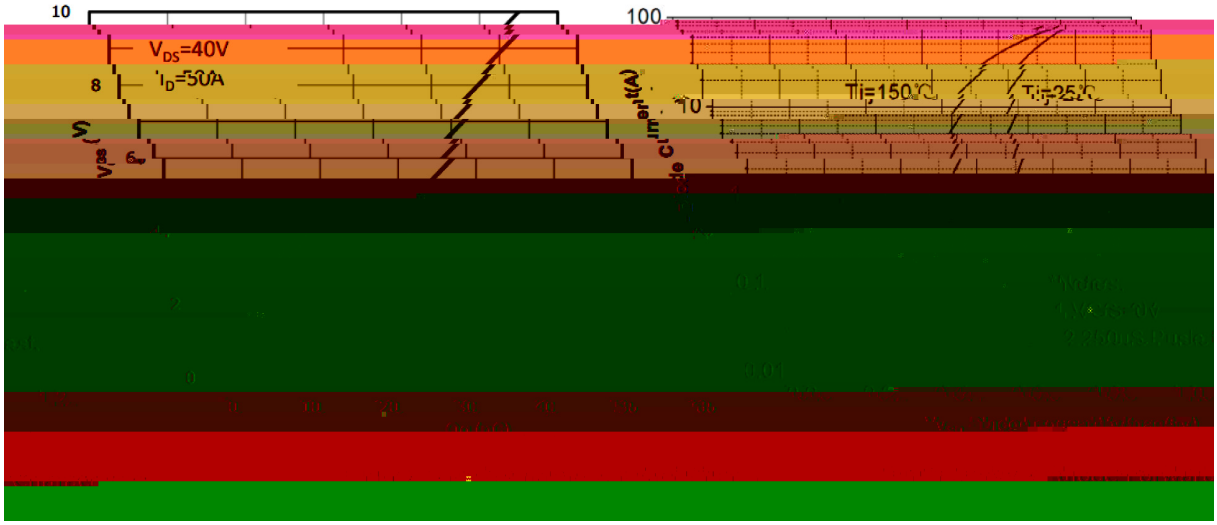
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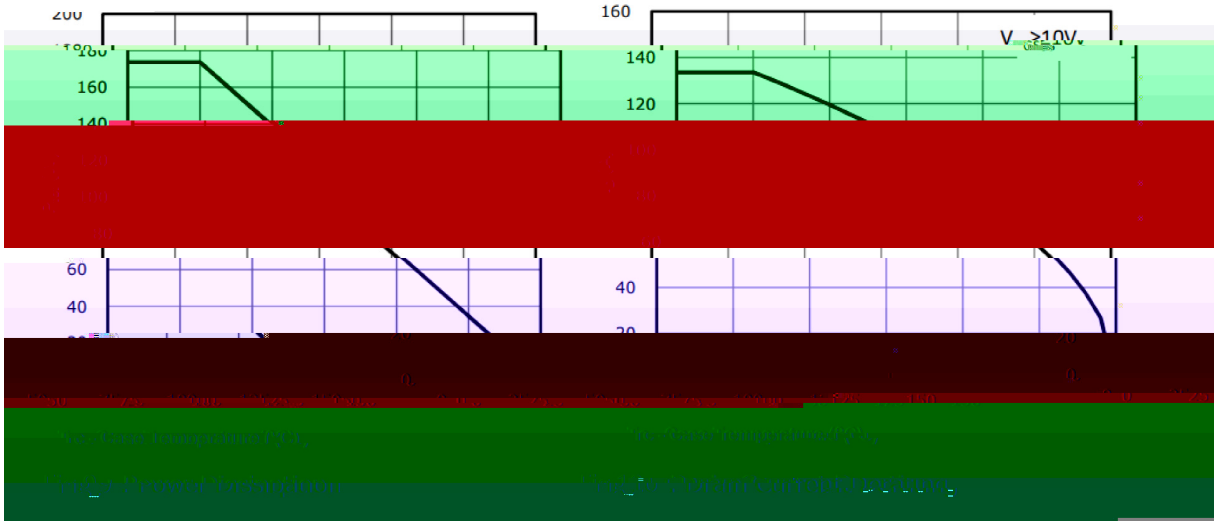

VGS=6V,6.5V,8V,10V
Notes:
2. Tj=25 ℃
VGS=5.5V
VGS=5V
Tj=125℃
I_D (A)
V_{DS} (V)
V_{GS} (V)

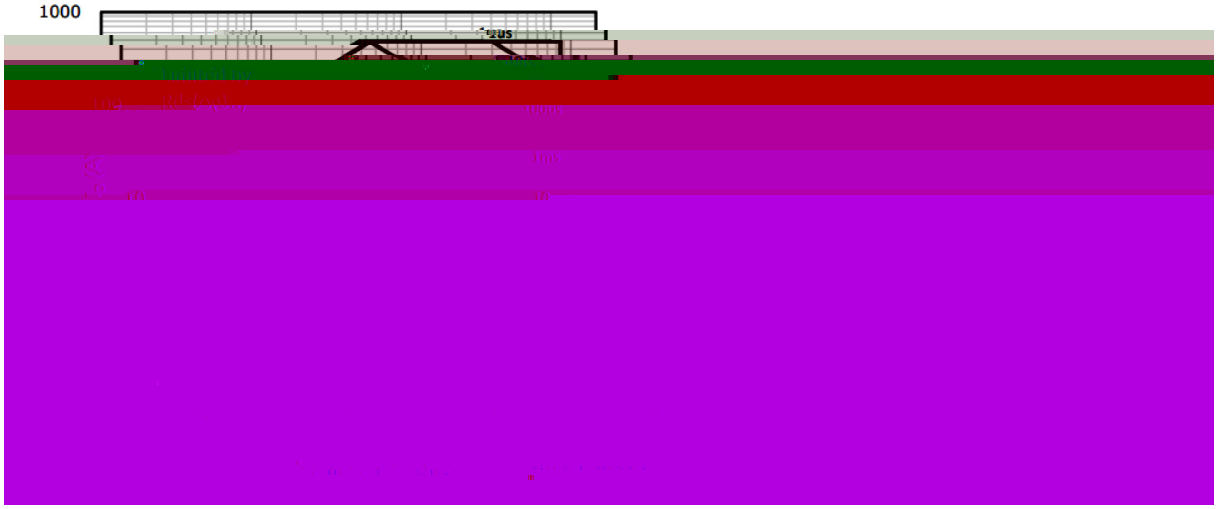

25℃
V_{GS} (V)
I_D (A)


V_{GS}=10V
I_D=5UA
Ciss
Coss
f=1MHz
V_{DS}(V)

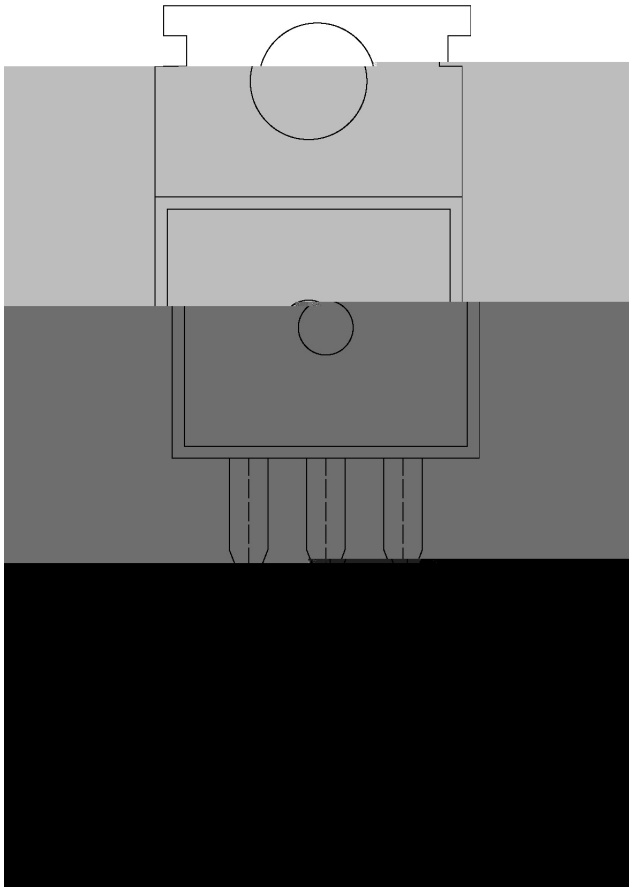
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y ÿ D Z W A k š ÿ D Z J

4 9 . y º Z W A

Note:

BR: Company Code

****: Lot No. Code, code change with Lot No.

G PD t … • Ž ¢ x /

ª ¢ y

1o• Ä ½ “ † 25 ½150 - k ž • 60 ½90sec;

2o• Q › “ † 255 r5 - k ž • 4 Ò 5 r0.5sec;

3o•D N ò i Ò 0 , † 2 ½10 - /sec.

Note:

1.Preheating:25~150 - , Time:60~90sec.

2.Peak Temp.:255 r5 - , Duration:5 r0.5sec.

3. Cooling Speed: 2~10 - /sec.

ÂD /Cã p ¯ »]

“ † y 270 r5 - ž • y 10 r1 sec. Temp.:270±5 Time:10±1 sec

G P á

• ^ x / BULK

Package Type 7>û ˜ E	Units ;>û ¦H	Dimension ;>û p . (unit Æmm³)